

Description

REGENERATIVE CLOCK REPEATER

5 TECHNICAL FIELD

The invention relates to clock signal distribution within a memory integrated circuit, and more particularly to clock repeaters placed along clock line for recovering the logic levels of the clock signals.

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BACKGROUND ART

In a digital synchronous system, effective clock distribution is essential for the system to work properly. Unduly slow propagation of a clock signal may limit the ability of a system's components to maintain adequate synchrony with each other. Moreover, a degraded clock signal can cause the system to malfunction completely, even with otherwise flawless design and components. With reference to Fig. 1, a representative clock distribution line 100 includes a reference clock signal 102 having a low logical level V_L and a high logical level V_H , a clock input buffer or driver 104. The distribution line 100 has an intrinsic resistance (R) and capacitance (C), 106, and a load capacitance 108 at the receiving end. The clock signal 102 is completely specified by a periodic high and low voltage levels (V_H and V_L), ideally with a square waveform.

When the resistance R of the line is comparable to or larger than the ON resistance of the driver, the propagation delay t_d is proportional to the RC time constant value. Because both resistance R and capacitance C increase linearly with length, this propagation delay t_d increases proportionally to the square of the line length.

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The degradation of the clock signal 102 is caused by the RC time constant of the clock distribution line 100 connecting the input buffer 104 to the gates having load capacitance C_L 108. The clock signal 102 suffers degradation to the point that its original high V_H and low V_L values are distorted out of their original values. This is illustrated by an output clock signal 110. The RC component in the distribution line 100 acts as a low pass filter that causes the clock signal 102 to have a rise time and fall time proportional to the time constant RC. As a result, the clock signal 102 does not retain the original clock signal waveform. Therefore, a clock distribution network that minimizes propagation delay and signal degradation of a clock signal is needed.

There exist different approaches attempting to solve the above problem. Each approach depends on different intrinsic resistance and capacitance values of the clock distribution line 106. In one approach, the line is divided into smaller sections so that the time delay t_d is approximately linear with length, instead of the square of the length. With reference to Fig. 2A, the clock distribution line 200A is divided into k segments. The objective of this prior art approach is to find the optimum number of segments k that will minimize the propagation delay t_d .

Assume that total line resistance is R and total line capacitance is C . Each segment of the line is bounded by a minimum size inverting buffer or driver 204A with a characteristic input capacitance C_i , 202A, and a characteristic output impedance R_o , 206A. Each segment also has a distributed RC characteristic 208A. The distributed resistance R_s , 208A, of each segment equals to R/k , and the distributed capacitance C_s of each segment equals to C/k , assuming all segments are of the same length. The 50% propagation delay (the time at which

Vout/Vin = 0.5 in Fig. 3) can be expressed as $T_{50\%} = k[0.7R_0(C_s+C_i) + R_s(0.4C_s + 0.7C_i)]$, where the factor 0.7 refers to the RC term made of lumped resistance and capacitance (here R_0 and C_i) and the factor 0.4 refers to the RC term made of a distributed resistance and capacitance (here R_s and C_s). The minimum value of $T_{50\%}$ gives the optimal k value, $K_{opt} = \sqrt{0.4 RC/0.7R_0C_i}$. For this optimal k value, the delay of a single segment connecting two inverters is equal to that of the single inverter, $0.4R_sC_s=0.7R_0C_i$.

With reference to Fig. 2B, in another approach, the propagation delay t_d can be further improved by increasing the size of the repeaters 204B by a factor h. The input capacitance 202B is now hC_i , the output impedance 201B is now R_0/h , and the distributed RC component 208B remains unchanged. In this case, the optimal values for k and h become: $K_{opt} = \sqrt{0.4RC/0.7R_0C_i}$, and $H_{opt} = \sqrt{R_0C/RC_i}$.

Fig. 3 illustrates the effect of lumped and distributed RC characteristic of clock distribution lines on the clock signal 300. In Fig. 3 the effect of the lumped RC is worse than that of the distributed RC on the clock signal 300. It takes the output voltage of a received clock signal 0.7 RC of time to reach 0.5 of its high logic value for a lumped-RC line 302, while it only takes the output voltage only 0.4 RC to reach the same level for a distribution-RC line 304. The severe effect of a lumped RC line 302 on the clock signal is ameliorated by the approach taken in Fig. 2B of increasing the repeater by an factor of h.

With reference to Fig. 4, another approach uses, instead of a single-inverter repeaters, repeater drivers made up of pairs of inverters 402 and 404 connected in series. In this way, the polarity of the clock signal traveling along the distribution line

segment 406 remains the same at any point along the clock distribution line 400.

5 In all of the approaches described above, the repeater structure needs the clock signal received at a repeater input to cross the threshold of the inverter in order to work. If the RC value of the distribution line is very high, the k_{opt} value will be great and the minimum propagation delay at this optimum value will still be large.

10 An object of the present invention is to provide repeater structure for a clock distribution line that reduces the total propagation delay compared to prior repeater structure.

15 SUMMARY OF THE INVENTION

The object of the invention is achieved by a regenerative clock repeater that uses an output driver means which receives information about the rising edge and falling edge to recover a high logical level (V_H) and a low logical level (V_L) of a clock signal. In order to achieve the above objective, the regenerative clock repeater comprises an edge detector that generates a pull-up control signal whenever it senses the rising edge and a pull-down control signal whenever it senses the falling edge of the clock signal. In the preferred embodiment of the invention, in the edge detector a high-threshold-level inverter and a low-threshold-level inverter are used to generate pull-up and pull-down control signals. The relative timing of these control signals with respect to the clock signal edges may be kept fixed by a plurality of logic gates and a latch. An output driver is triggered by the pull-up control signal and the pull-down control signal to recover the high logical level (V_H) and the low logical level (V_L) of the clock signal.

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BRIEF DESCRIPTION OF THE DRAWINGS

Fig. 1 illustrates a schematic diagram of a clock signal coupled to a representative distribution line of the prior art having intrinsic RC characteristics.

Fig. 2A illustrates a schematic diagram of a multistage circuit of the prior art to reduce the propagation delay t_d caused by intrinsic resistance and capacitance in the clock distribution line.

Fig. 2B illustrates schematic diagram of another approach of the prior art to further reduce the propagation delay caused by intrinsic resistance and capacitance in the clock distribution line by increasing the h factor of the repeater.

Fig. 3 illustrates graphs of the effects of the lumped and distributed RC characteristic of a clock distribution line on the clock signal.

Fig. 4 illustrates a schematic diagram of yet another prior art approach using repeaters made up of inverter pairs connected in series in a clock distribution line to keep the polarity of the clock signal the same at any point of the line.

Fig. 5 is a schematic block diagram illustrating the general features of a regenerative clock repeater circuit in accord with the present invention.

Fig. 6 is a schematic circuit diagram of a preferred embodiment of the edge detector used in the repeater circuit of Fig. 5.

Figs. 7A and 7B are graphs illustrating the operation of the high and low trigger point inverter used in the edge detector in Fig. 6.

Fig. 8 illustrates a signal timing diagram showing operation of the circuit of elements of a regenerative clock repeater of Figs. 5 and 6 according to the present invention.

Fig. 9 illustrates a memory device that uses the regenerative clock repeaters as described in Fig. 5.

PREFERRED EMBODIMENT OF THE DESCRIPTION

5 With reference to Fig. 5, a regenerative clock repeater 700 according to the present invention, that recovers the low logical level (V_L) and a high logical level (V_H) of a degraded clock signal, comprises an edge detector circuit 500 and an output driver circuit 706.

10 The edge detector circuit 500 receives a clock signal CK_{IN} from a segment of clock distribution line 702 characterized by an intrinsic RC impedance 704 and generates either a pull-up control signal (PULL-UP#) or a pull-down control signal (PULL-DOWN) based on the logic

15 level of the clock signal 702. The pull-up control signal (PULL-UP#) is generated by a sensed rising edge of the clock signal passing above a low threshold voltage level, the pull-down control signal (PULL-DOWN) is generated by a sensed falling edge of the clock signal

20 passing below a high threshold voltage level. The output driver 706 has a pull-up transistor 706A (usually p-type) connected to a power supply at a high logical level (V_H) and a pull-down transistor 706B (usually n-type) connected to a power supply at a low logical level (V_L),

25 typically ground. The pull-up and pull-down transistors 706A and 706B, respectively, receive the pull-up control signal and the pull-down control signal to recover the high logical level (V_H) and a low logical level (V_L) of the received degraded clock signal and place the

30 recovered clock onto another segment of the clock distribution line which is likewise characterized by an intrinsic RC impedance 709 and whose output is the Ck_{out} at node 710.

35 With reference to Fig. 6, the edge detector 500 includes a high-threshold-level inverter (IVH) 540 and a

low-threshold-level inverter (IVL) 550, both coupled to a clock input 502. The high-threshold-level inverter 540 generates a first signal (HIGH#) and also an inverse of this signal (HIGH) via an inverter 546. The low-
5 threshold-level inverter (IVL) generates a second signal (LOW#) and also an inverse of this signal (LOW) via an inverter 556. These four signals are input into NOR logic gates 562 and 564, the outputs of which are input into a set/reset latch 566. The output of latch 566,
10 together with the four (HIGH, HIGH#, LOW, LOW#) signals, are input into NAND and NOR logic gates 568 and 570 to generate the pull-up control signal (PULL-UP#) and the pull-down control signal (PULL-DOWN#).

The high-threshold-level inverter (IVH) 540 is
15 made up of a low threshold p-channel transistor 542 and a high threshold n-channel transistor 544. The low-threshold-level PMOS transistor 542 is used as a pull-up transistor with its source connected to a voltage supply. The high-threshold level NMOS transistor 544 is used as a
20 pull-down transistor with its source connected to an electrical ground. The gates of the low-threshold PMOS transistor 542 and the high-threshold level pull-down NMOS transistor 544 are both connected to the clock input Ck. Finally, the drain of the low-threshold PMOS
25 transistor 542 and the drain of the NMOS transistor 544 together form an inverter output producing the signal HIGH#.

Fig. 7A illustrates the transfer function characteristics of a high-threshold-level inverter (IVH) 540 used in this invention. The low-threshold PMOS
30 transistor 542 and the high-threshold NMOS transistor 544 in the high-threshold-level inverter (IVH) 540 cause the threshold voltage V_{th} to be very high and the distance between V_{th} and V_H to be very narrow. This is illustrated
35 by the curve 540A.

Returning to Fig. 6, the low-threshold-level inverter (IVL) 550 comprises high-threshold-level PMOS transistor 552 acting as a pull-up transistor coupled with a low-threshold-level NMOS 554 acting as a pull-down transistor. The low-threshold-level inverter (IVL) 550 generates the second signal (LOW#) by detecting a rise above a predetermined low logical level (V_L) on the input clock signal 502. The second signal (LOW#) is input into the inverter 556 to generate the inverse signal (LOW).

In the low-threshold-level inverter (IVL) 550, a low-threshold-level NMOS transistor 554 is used as a pull-down transistor with its source connected to the electrical ground 547. A high-threshold-level PMOS transistor 552 is used as a pull-up transistor with its source connected to the power supply 543. The gates of the high-threshold-level PMOS transistor 552 and of the low-threshold-level NMOS transistor 554 are both connected to the clock signal input 502. Finally, the drain of the high-threshold-level PMOS transistor 552 and the drain of the low-threshold-level NMOS transistor 554 together form an inverter output producing the signal LOW.

In Fig. 7B, the transfer function of the low-threshold-level inverter (IVL) 550 is seen to be the opposite of the high-threshold-level inverter (IVH) 540. Unlike the high-threshold-level inverter (IVH) 540, the low-threshold-level inverter (IVL) 550 has a low-threshold voltage (V_{th}) to detect transitions of the clock signal 502. The distance between V_{th} to V_H is very large.

The output of the high-threshold-level detector (IVL) 540 HIGH# and that of the low-threshold-level detector (IVH) 550 LOW# are input into a first NOR gate 562. The output of the first NOR gate 562 is input to a reset terminal of a set/reset latch 566. The inverse outputs HIGH and LOW are input into a second logic NOR

gate 564. The output of the second NOR gate 564 is input into the set terminal of the set/reset latch 566. Output of the set/reset latch 566 is called RISE signal. This signal RISE indicates whether the edge of the clock signal 502 is rising or falling. In general, the set/reset latch 566 only goes HIGH when the set terminal is HIGH and goes LOW when reset terminal is HIGH. When both set and reset terminals are LOW or zero, the latch 566 retains its previous value, $Q_{n+1} = Q_n$.

Together with the inverter signals HIGH# and LOW, the RISE signal is input into a first NAND gate 568 to provide a pull up control signal (PULL_UP#). The signals HIGH, LOW#, and RISE are input into a third NOR logic gate 570 to produce a pull-down control signal (PULL_DOWN).

With reference to Fig. 8, curve 800A illustrates the clock signal at the input 502 in Fig. 5. This received clock signal is defined by its low (V_L) and high (V_H) logical levels, but has degraded due to the RC characteristic of the clock distribution line along which it has propagated, and thus has a ramped waveform with relatively long rise and fall times instead of well-defined edge transitions. The high-threshold-level inverter (IVH) 540 detects clock transitions across the high-threshold level (V_{TH}) near the high logical level V_H , while the low level inverter (IVL) detects clock transitions across the low-threshold line (V_{TL}) near the low logical level V_L . During the rising of the clock, a transition across the low-threshold level (V_{TL}) occurs at t_0 and again later at t_4 . A transition across the high-threshold level (V_{TH}) occurs at t_1 (and again later at t_5). The period between t_0 and t_1 is characterized by a pulse of the pull up control signal (PULL-UP#), shown in curve 800E. During the fall of the clock, a transition across the high-threshold level (V_{TH}) occurs at time t_2 (and at

later times not shown after t_5). A transition across the low-threshold level (V_{TL}) occurs at t_3 (and again later times now shown). The time period between t_2 and t_3 is characterized by a pulse of the pull-down control signal (PULL-DOWN), shown in curve 800F.

5 With reference to curve 800B, as the input clock signal CK, 800A, crosses the low logical level V_L , the low trigger point inverter 550 pulls its output LOW# to ground and its complement LOW goes high, as seen for
10 signal 800B. The edges of LOW signal are at t_0 and t_3 .

Referring to curve 800C, as the clock signal Ck increases, the low-threshold level PMOS 542 is conducting and thus the output HIGH# is at V_H . During this time the high-threshold level NMOS 544 does not conduct. Only
15 when the clock signal 502 reaches V_{TH} , the low-threshold PMOS 544 can prevent current from flowing across the channel and becomes non-conducting. In the mean time, the high-threshold NMOS becomes conduct. As a result, the high-threshold level NMOS 544 takes over and pull the
20 output (HIGH#) to low. In Fig. 800C, the graph for HIGH represents the inverse of the HIGH# output. The edges of HIGH signal are at t_1 and t_2 respectively.

With reference to curve 800D, the output response RISE of the set/reset latch 566 is illustrated.
25 The set terminal of the latch 566 is HIGH when both HIGH, LOW terminals of the NOR gate 564 are LOW. On the other hand, the reset is only HIGH when both HIGH#, LOW# are LOW logic or zero. The falling edge of the RISE signal is at t_1 , indicating the clock rise has terminated. The
30 rise edge of the RISE signal is at t_3 , indicating the fall edge of the clock has terminated.

Graph 800E illustrates the pull-up control signal (PULL_UP#) and the manner it senses the rising edge of the clock signal shown in graph 800A. Also, the

pulse duration of the pull-up control signal indicates the time distance between t_0 and t_1 .

5 Graph 800F illustrates the pull-down control signal (PULL_DOWN) and the manner it detects the falling edge of the clock signal shown in graph 800A. The pulse duration of the fall down control signal indicates the time distance between t_2 and t_3 .

10 With reference to Fig. 9, a synchronous memory device 1000 includes regenerative clock repeaters 500 as described above to regenerate the clock signal on clock lines at different locations of the memory device 1000. This illustrates a typical use for the clock repeaters in integrated circuitry. A typical memory device 1000 includes a memory array 1002, a control circuit 1004, a
15 row decoder 1006, a column decoder 1010, sensing and writing circuit 1008 and 1012, a clock circuit 1014. Regenerative clock repeaters 500 are distributed throughout the device 1000 along clock distribution lines, which are divided into segments.